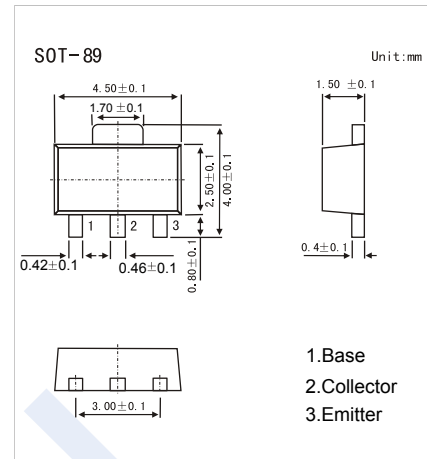


## NPN Transistors

## 2SC2873

## ■ Features

- Small Flat Package
- High Speed Switching Time
- Low Collector-emitter saturation voltage
- Complementary to 2SA1213

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	50	V
Collector - Emitter Voltage	$V_{CE0}$	50	
Emitter - Base Voltage	$V_{EB0}$	5	
Collector Current - Continuous	$I_C$	2	A
Collector Power Dissipation	$P_C$	500	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CB0}$	$I_C = 100\mu\text{A}$ , $I_E = 0$	50			V
Collector- emitter breakdown voltage	$V_{CE0}$	$I_C = 1\text{mA}$ , $I_B = 0$	50			
Emitter - base breakdown voltage	$V_{EB0}$	$I_E = 100\mu\text{A}$ , $I_C = 0$	5			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = 50\text{V}$ , $I_E = 0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 5\text{V}$ , $I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 1\text{A}$ , $I_B = 50\text{mA}$			0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 1\text{A}$ , $I_B = 50\text{mA}$			1.2	
DC current gain	$h_{FE}$	$V_{CE} = 2\text{V}$ , $I_C = 0.5\text{A}$	70		240	
		$V_{CE} = 2\text{V}$ , $I_C = 2\text{A}$	20			
Collector output capacitance	$C_{ob}$	$V_{CB} = 10\text{V}$ , $I_E = 0$ , $f = 1\text{MHz}$		30		pF
Transition frequency	$f_T$	$V_{CE} = 2\text{V}$ , $I_C = 0.5\text{A}$		120		MHz

■ Classification of  $h_{FE}(1)$ 

Marking	MO	MY
Rank	O	Y
Range	70-140	120-240

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### Typical Characteristics

